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Sheet 1 of 1

Complete if Known

Application Number	10/649,712
Filing Date	August 26, 2003
First Named Inventor	Ren, Fan
Art Unit	2812
Examiner Name	
Attorney Docket Number	5853-274

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² #			
		US- 2002/0052076 A1	May 2, 2002	Khan et al.	
		US- 8,429,487 B1	Aug. 6, 2002	Ando	
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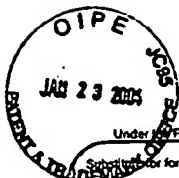
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		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				

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Filing Date August 26, 2003
First Named Inventor Ren, Fan
Art Unit 2812
Examiner Name
Attorney Docket Number 5853-274

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Kim et al., "Inversion behavior in Sc2O3/GaN gated diodes," Appl. Phys. Lett., 81: 373-375, July 2002.	
		Simin et al., "7.5kW/mm2 current switch using AlGaIn/GaN metal-oxide-semiconductor heterostructure field effect transistor on SiC substrates," Electronics Letters, 36: November 2000.	
		Mistele et al., "First AlGaIn/GaN MOSFET with photoanodic gate dielectric," Materials Science and Engineering, B93, 107-111, 2002.	
		Khan et al., "Enhancement and depletion mode GaN/AlGaIn hetrostructure field effect transistors," Appl. Phys. Lett., 68: 514-516, January 1996.	
		Simin, et al., "SiO2/AlGaIn/InGaIn/GaN MOSDHFTs," IEEE Electron Device Letters, 23: 458-460, August 2002.	
		Kim et al., "Characteristics of MgO/GaN gate-controlled metal-oxide-semiconductor diodes," Applied Physics Letter, 80: 4555-4557, June 2002.	
		Koudymov et al., "Maximum current in nitride-based hetrostructure field-effect transistors," Applied Physics Letters, 80: 3216-3218, April 2002.	
		Hu et al., "Si3N4/AlGaIn/GaN-metal-insulator-semiconductor hetrostructure field-effect transistors," Applied Physics Letters, 79: 2832-2834, October 2001.	
		Teles et al., "Spinodal decomposition in BxGa1-xN and BxAl1-xN alloys," Applied Physics Letters, 80: 1177-1179, February 2002.	
		Chou et al., AlGaIn/GaN Metal Oxide-Semiconductor Hetrostructure Field-Effect Transistor Based on a Liquid Phase Deposited Oxide," Jpn. J. Appl. Phys. 41: L748-L750, July 2002.	

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